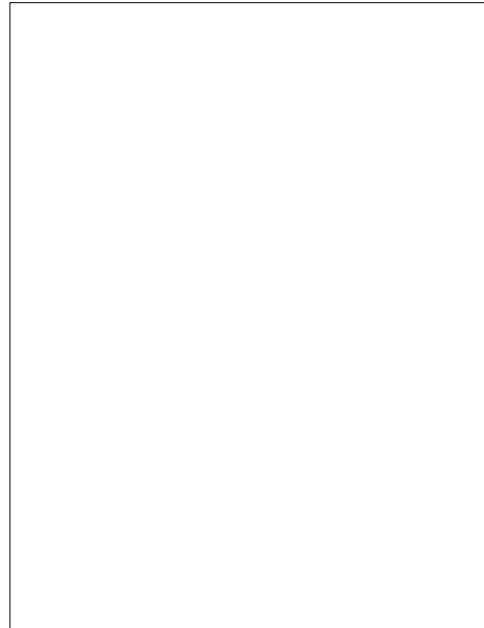


DESCRIPTION:

The 100-8 SCR provides high dV/dt rate with strong resistance to electromagnetic interface. It is especially recommended for use on residual current circuit breaker, straight hair, igniter etc. Package SOT-223 is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM} / V_{RRM}	800	V
I_{GT}	"200	A

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125 ⁷	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
Average on-state current ($T_C 090^\circ\text{C}$)	$I_{T(AV)}$	0.6	A
RMS on-state current ($T_C 090^\circ\text{C}$)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	12	A
Non repetitive surge peak on-state current ($t_p=8.3\text{ms}$, $T_j=25^\circ\text{C}$)		13	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	0.72	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	100	A/s
Peak gate current ($t_p=20^\circ\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	1	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.1	W

Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.8)	V_{pp}	1	kV

NOTE 1: Operating junction temperature T_j is up to 125 when a resistor "1k" is connected between Gate and Cathode. Without this resistor, the T_j is up to 110 only.

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L=33$	-	40	200	A
V_{GT}		-	0.6	0.8	V
V_{GD}	$V_D=V_{DRM} T_j=125$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	-	

MARKING

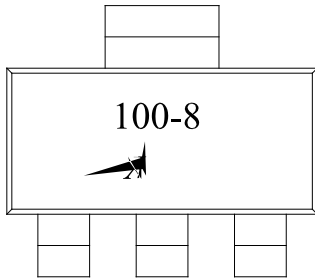
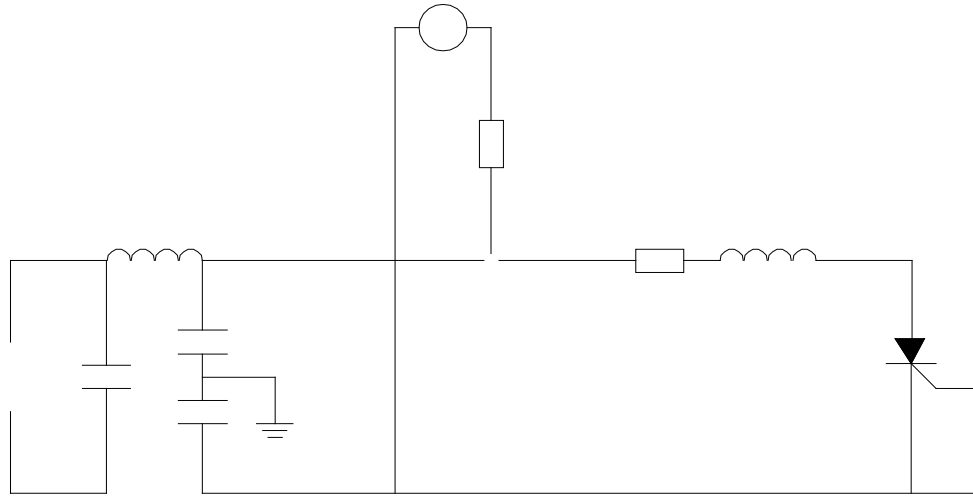


FIG.8 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.



DELIVERY MODE

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	-		12.30	-		0.482
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
D0		1.55	1.60		0.061	0.063
D1		-	-			
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.95	2.00	2.05	0.077	0.079	0.081
10P0	39.80	40.00	40.20	1.567	1.575	1.583
A0	6.85	6.95	7.05	0.269	0.273	0.276
B0	7.15	7.25	7.35	0.280	0.284	0.288
K0	1.95	2.05	2.15	0.076	0.080	0.084
T	0.20	0.25	0.30	0.008	0.010	0.012

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